

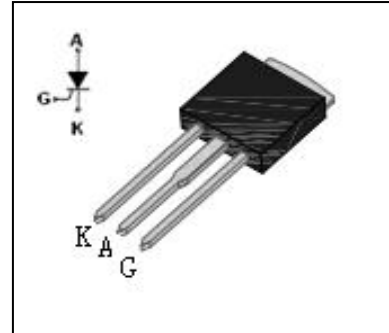
P/N: YZPST-BT151U SCR

● Package

T0-251

● Main Feature (T_j=25°C)

Symbol	Value	Unit
I _{T(RMS)}	12	A
V _{DRM} / V _{RRM}	600/800	V
I _{GT}	2 to 15	mA



● Absolute ratings (Limiting Values)

Symbol	Parameter	Value	Unit
I _{T(RMS)}	RMS on-state current (180° conduction angle)	12	A
I _{T(AV)}	AV on-state current (180° conduction angle)	7.5	A
I _{TSM}	Non repetitive surge peak on-state Current (tp=10ms)	100	A
I ² t	(tp=10ms)	50	A ² S
I _{GM}	Peak gate current(tp=20us)	2	A
P _{GM}	Peak gate power	5	W
P _{G(AV)}	Average gate power	0.5	W
T _{stg}	Storage temperature	-40--+150	°C
T _j	Operating junction temperature	-40--+125	

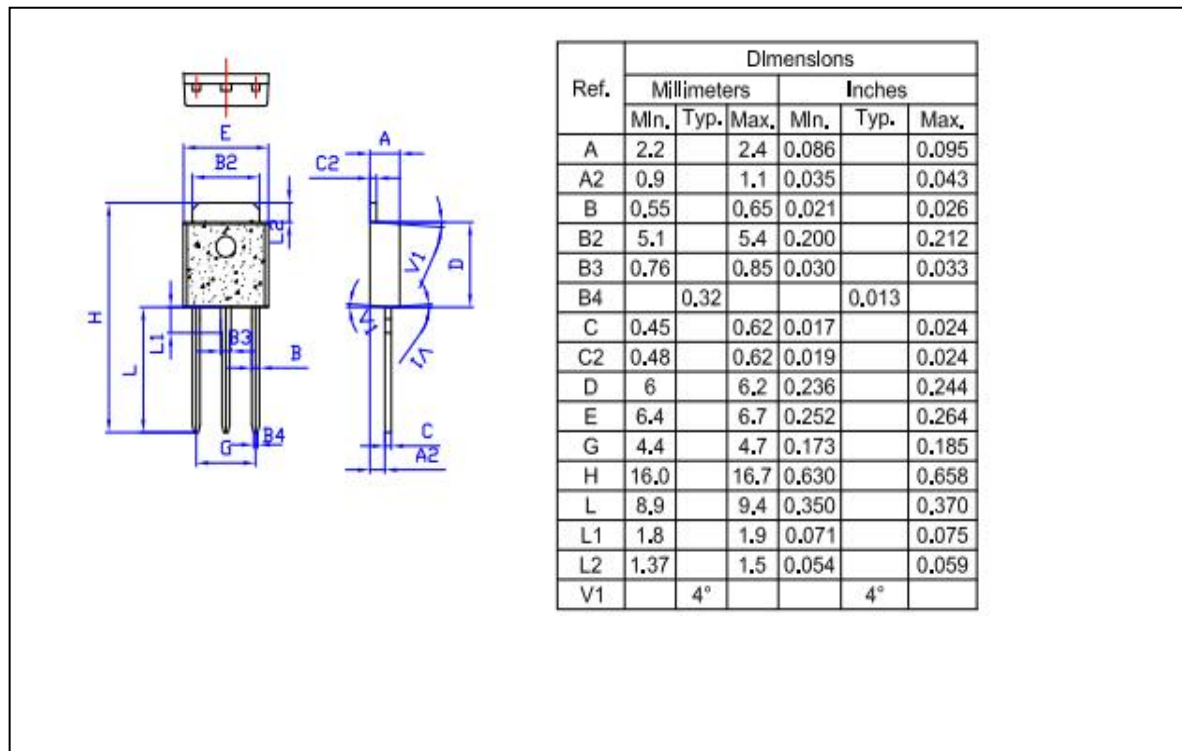
● Thermal Resistances

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case	1.3	K/W
R _{th(j-a)}	Junction to ambient	60	K/W

● Electrical characteristics (Tj=25°C unless otherwise stated)

Symbol	Test Conditions		Value			Unit
			Min	Type	Max	
I _{GT}	V _D =6V, R _L =100 Ω		2	5	15	mA
V _{GT}	V _D =12V, R _L =100 Ω		-----	0.7	0.8	V
V _{GD}	V _D =V _{DRM} , R _L =3.3K Ω Tj=110°C		0.2	-----	-----	V
I _H	I _T =100mA Gate Open		-----	9	20	mA
dV/dt	V _D =67%V _{DRM} , GateOpen, Tj=125°C		200	-----	-----	v/ μ s
V _{TM}	I _T =16A, tp=380 μ s		-----	-----	1.7	V
I _{DRM}	V _D =V _{DRM}	Tj=25°C	-----	-----	10	uA
I _{RRM}	V _R =V _{RRM}	Tj=125°C	-----	-----	1	mA

● Measure of package (TO-251 型)



●Electrocircuit:

